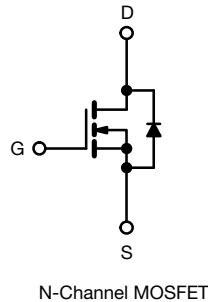
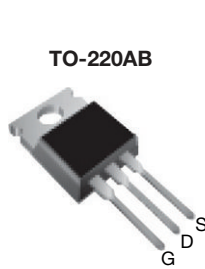


EF Series Power MOSFET with Fast Body Diode

PRODUCT SUMMARY		
V_{DS} (V) at T_J max.	650	
$R_{DS(on)}$ max. at 25 °C (Ω)	$V_{GS} = 10$ V	0.176
Q_g (Max.) (nC)	84	
Q_{gs} (nC)	14	
Q_{gd} (nC)	24	
Configuration	Single	



FEATURES

- Fast body diode MOSFET using E series technology
- Reduced t_{rr} , Q_{rr} , and I_{RRM}
- Low figure-of-merit (FOM): $R_{on} \times Q_g$
- Low input capacitance (C_{iss})
- Increased robustness due to low Q_{rr}
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Telecommunications
 - Server and telecom power supplies
- Lighting
 - High intensity discharge (HID)
 - Light emitting diodes (LEDs)
- Consumer and computing
 - ATX power supplies
- Industrial
 - Welding
 - Battery chargers
- Renewable energy
 - Solar (PV inverters)
- Switch mode power supplies (SMPS)
 - LLC
 - Phase shifted bridge (ZVS)
 - 3-level inverter
 - AC/DC bridge

ORDERING INFORMATION	
Package	TO-220AB
Lead (Pb)-free and Halogen-free	SiHP21N60EF-GE3


ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V_{DS}	600	V	
Gate-Source Voltage	V_{GS}	± 30		
Continuous Drain Current ($T_J = 150$ °C)	V_{GS} at 10 V	$T_C = 25$ °C	21	A
		$T_C = 100$ °C	14	
Pulsed Drain Current ^a	I_{DM}	53		
Linear Derating Factor		1.8	W/°C	
Single Pulse Avalanche Energy ^b	E_{AS}	367	mJ	
Maximum Power Dissipation	P_D	227	W	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C	
Drain-Source Voltage Slope	dV/dt	70	V/ns	
Reverse Diode dV/dt ^d				
Soldering Recommendations (Peak Temperature) ^c	for 10 s	300	°C	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω , $I_{AS} = 5.1$ A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, $dI/dt = 900$ A/ μ s, starting $T_J = 25$ °C.



THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	TYP.	MAX.	UNIT	
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.55		

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		600	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 1\text{ mA}$		-	0.59	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
		$V_{GS} = \pm 30\text{ V}$		-	-	± 1	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 480\text{ V}, V_{GS} = 0\text{ V}$		-	-	1	μA
		$V_{DS} = 480\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	500	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 11\text{ A}$	-	0.153	0.176	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 30\text{ V}, I_D = 11\text{ A}$		-	7	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V},$ $V_{DS} = 100\text{ V},$ $f = 1\text{ MHz}$		-	2030	-	pF
Output Capacitance	C_{oss}			-	105	-	
Reverse Transfer Capacitance	C_{rss}			-	5	-	
Effective output capacitance, energy related ^a	$C_{o(er)}$	$V_{GS} = 0\text{ V}, V_{DS} = 0\text{ V to } 480\text{ V}$		-	86	-	pF
Effective output capacitance, time related ^b	$C_{o(tr)}$			-	299	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 11\text{ A}, V_{DS} = 480\text{ V}$	-	56	84	nC
Gate-Source Charge	Q_{gs}			-	14	-	
Gate-Drain Charge	Q_{gd}			-	24	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 480\text{ V}, I_D = 11\text{ A}$ $R_g = 9.1\text{ }\Omega, V_{GS} = 10\text{ V}$		-	21	42	ns
Rise Time	t_r			-	31	62	
Turn-Off Delay Time	$t_{d(off)}$			-	59	89	
Fall Time	t_f			-	27	54	
Gate Input Resistance	R_g			$f = 1\text{ MHz}, \text{open drain}$		0.2	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	21	A
Pulsed Diode Forward Current	I_{SM}			-	-	53	
Diode Forward Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 11\text{ A}, V_{GS} = 0\text{ V}$		-	0.9	1.2	V
Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 11\text{ A},$ $di/dt = 100\text{ A}/\mu\text{s}, V_R = 400\text{ V}$		-	135	270	ns
Reverse Recovery Charge	Q_{rr}			-	0.76	1.52	μC
Reverse Recovery Current	I_{RRM}			-	11	-	A

Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .
- b. $C_{oss(tr)}$ is a fixed capacitance that gives the charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

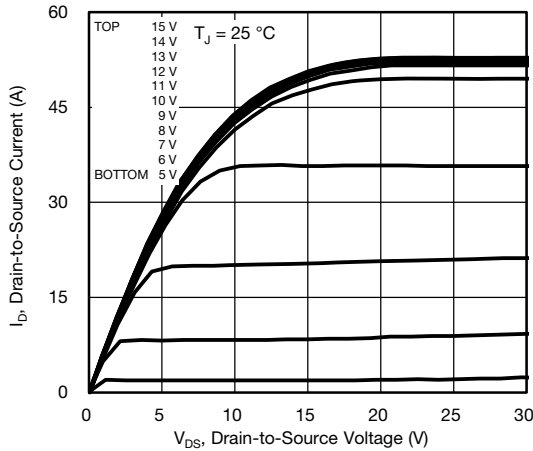


Fig. 1 - Typical Output Characteristics, $T_J = 25\text{ }^\circ\text{C}$

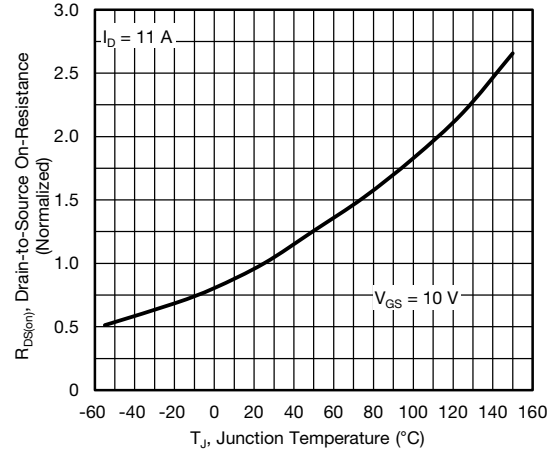


Fig. 4 - Normalized On-Resistance vs. Temperature

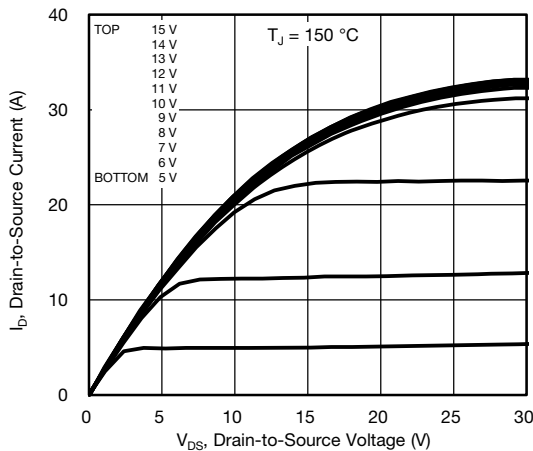


Fig. 2 - Typical Output Characteristics, $T_J = 150\text{ }^\circ\text{C}$

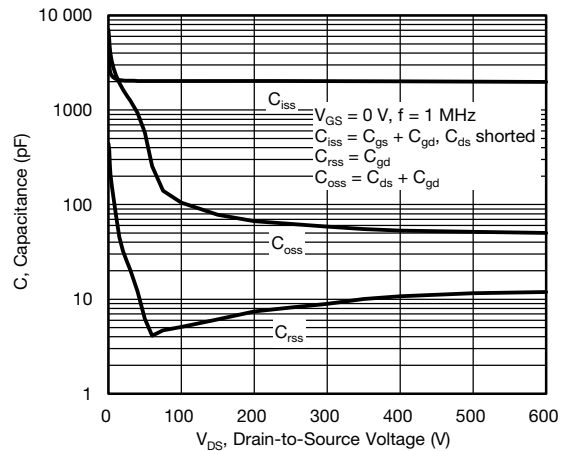


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

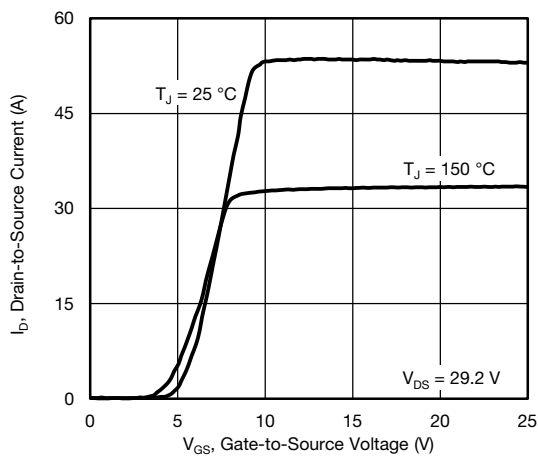


Fig. 3 - Typical Transfer Characteristics

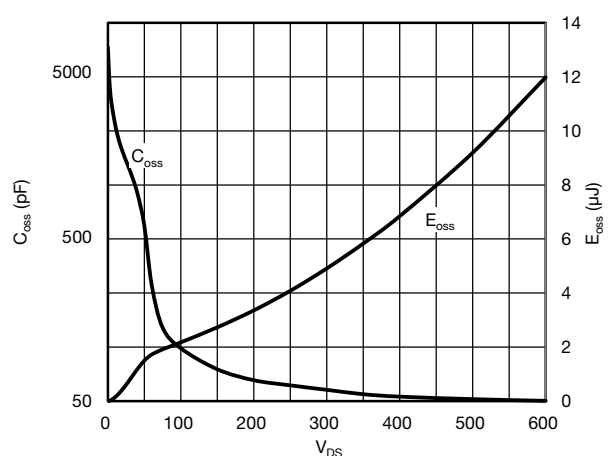


Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

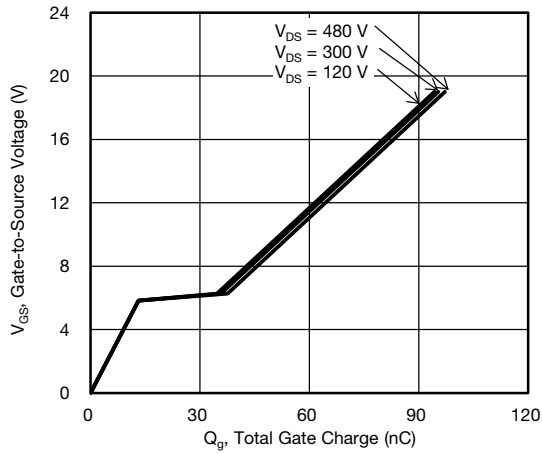


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

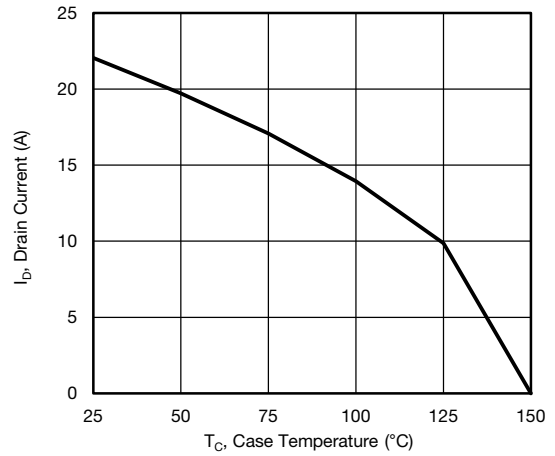


Fig. 10 - Maximum Drain Current vs. Case Temperature

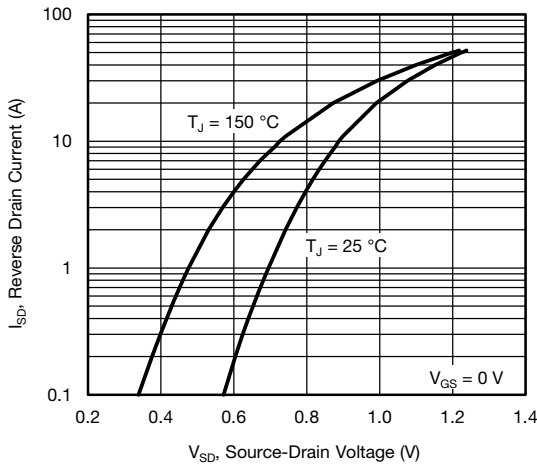


Fig. 8 - Typical Source-Drain Diode Forward Voltage

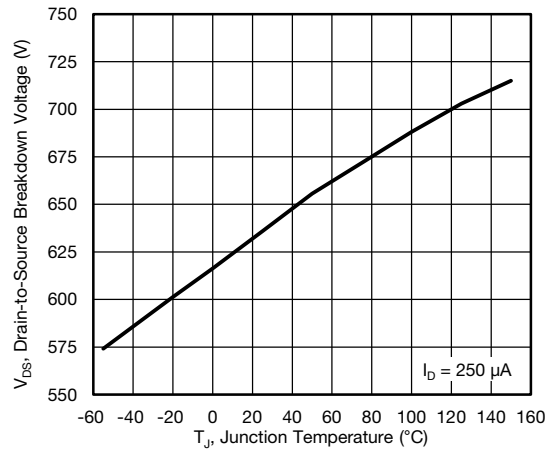


Fig. 11 - Typical Drain-to-Source Voltage vs. Temperature

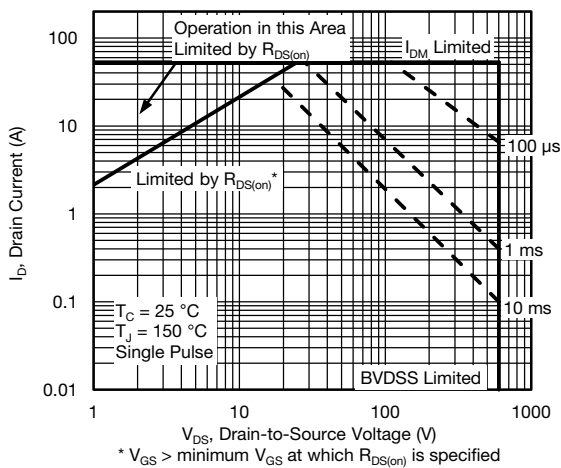


Fig. 9 - Maximum Safe Operating Area

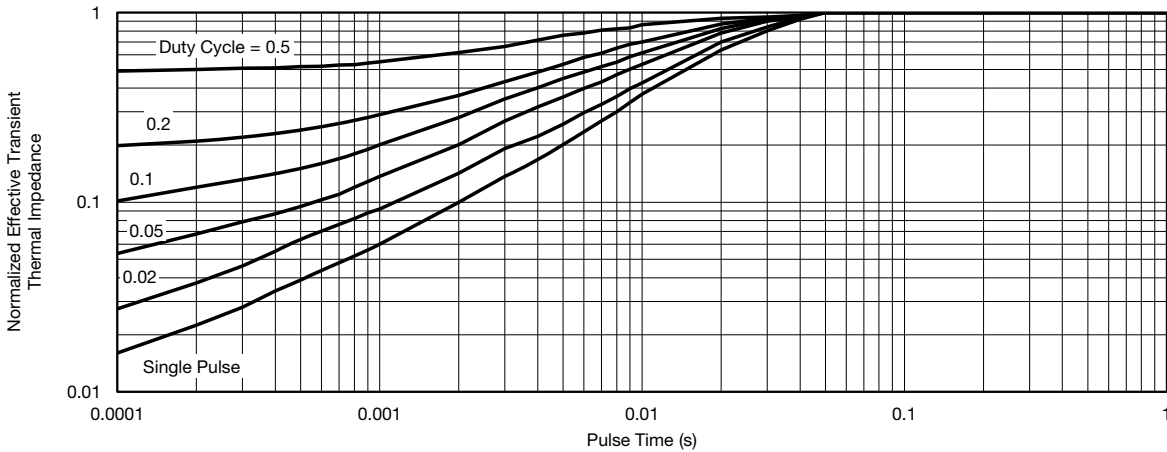


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

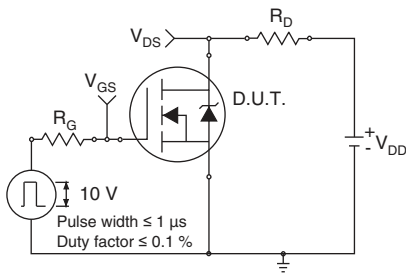


Fig. 13 - Switching Time Test Circuit

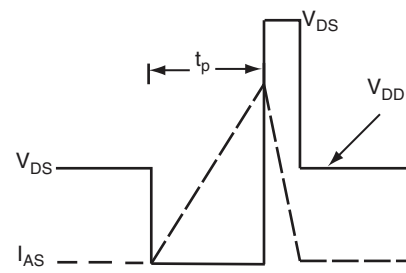


Fig. 16 - Unclamped Inductive Waveforms

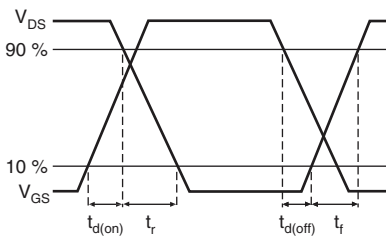


Fig. 14 - Switching Time Waveforms

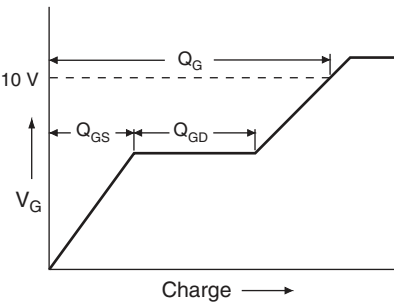


Fig. 17 - Basic Gate Charge Waveform

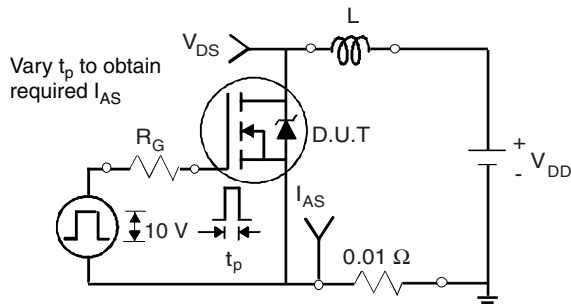


Fig. 15 - Unclamped Inductive Test Circuit

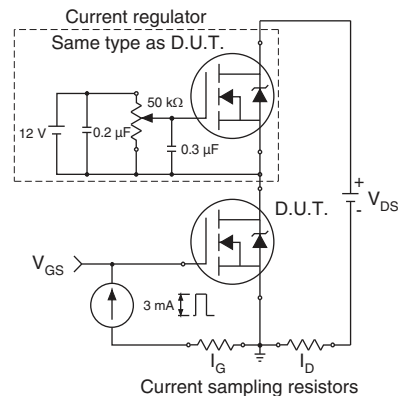
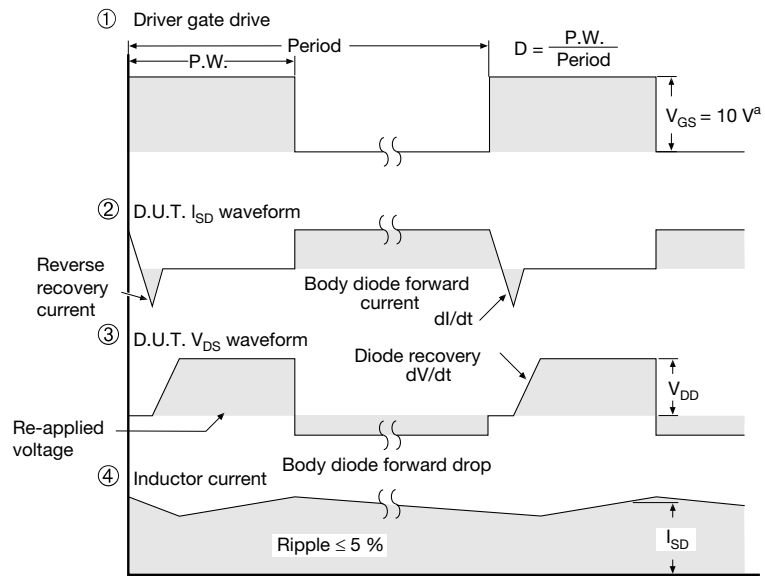
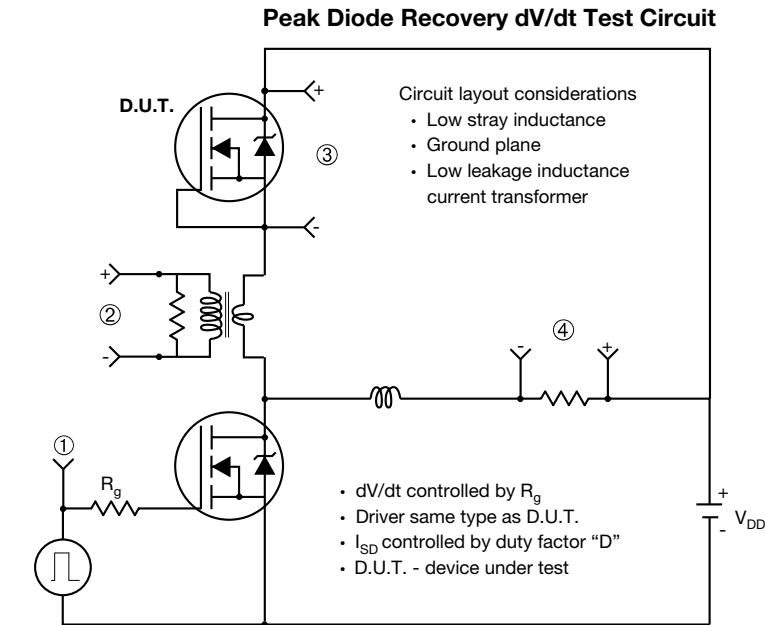


Fig. 18 - Gate Charge Test Circuit



Note
a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 19 - For N-Channel

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TO-220-1

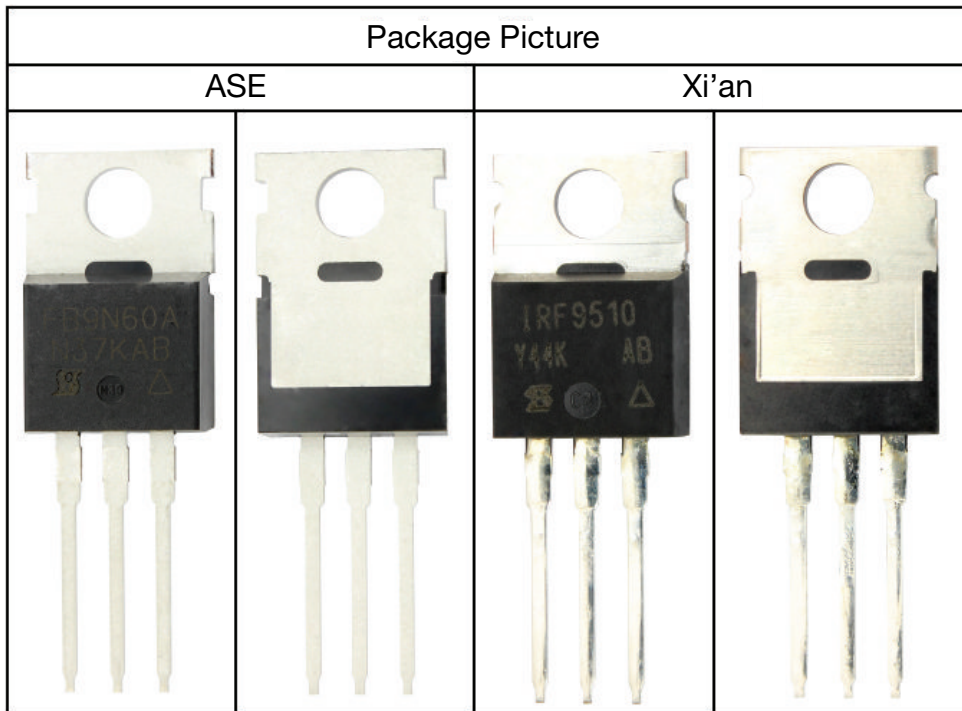


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
Ø P	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: X15-0364-Rev. C, 14-Dec-15
DWG: 6031

Note

- M* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM





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